application 09/114,847, now issued as U.S. Patent No. 6,201,276 B1. Also included are mixtures of any of the gases or types of gases described above. Exemplary non-plasma process parameters using these other gases include a flow rate of about 2 sccm to about 400 sccm for these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.--

In the Claims:

Please cancel claims 1-3, 76-90, and 99-101.

Please amend claims 91, 92, 94, and 102 as follows:

91. (Amended) A method of treating a semiconductor device, comprising:

providing a capacitor having a first plate, a dielectric over the first plate, and a second plate over the dielectric, the second plate including first and second conductive layers;

exposing said first conductive layer to a material selected from the group consisting of diborane, phosphine, methylsilane, hexamethyldisilane, and hexamethyldisilazane to reduce an ability of the first conductive layer to associate with oxygen; and

forming the second conductive layer on the first conductive layer, the second conductive layer being formed after the first conductive layer has been exposed to the material from the group.

92. (Amended) The method of claim 91, wherein providing a capacitor comprises providing an in-process capacitor; and the method further comprises providing a third conductive layer over the second conductive layer.